

IXTA3N120

IXTA3N120 Information





Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



IXTA3N120 Specifications

Manufacturer Part Number	IXTA3N120
Manufacturer	IXYS
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
Series	-
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	1200V
Current - Continuous Drain (Id) @ 25°C	3A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	10V
Vgs(th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	42nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	1350pF @ 25V
Vgs (Max)	$\pm 20 V$
FET Feature	-
Power Dissipation (Max)	200W (Tc)
Rds On (Max) @ Id, Vgs	4.5 Ohm @ 1.5A, 10V
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Surface Mount
Supplier Device Package	TO-263 (IXTA)
Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
	Report errors?

IXTA3N120 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE BUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTA3N120 Payment Methods



IXTA3N120 Shipping Methods



If you have any question about IXTA3N120, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com